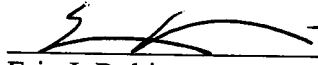


REMARKS

The specification has been corrected in accordance with 37 CFR §1.121.

Examination on the merits is requested.

Respectfully submitted,



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VERSION WITH MARKINGS TO SHOW CHANGES MADE

Please replace page 13, paragraph 3 as follows:

However, in the first embodiment, niobium oxide is used for the high-refractive-index film 13b of the end facet reflective film 13, and the light absorption coefficient of niobium oxide is lower than that of titanium oxide. Thus, a rise in temperature in the vicinity of the end facet of the resonant cavity 13 [12] can be suppressed. As a result, the crystallinity of the quantum well active layer 1 and the surrounding portions thereof is less likely to deteriorate, and the semiconductor laser device can increase its output power. The active layer has a quantum well structure in the illustrated embodiment but does not have to do so.

Please replace page 21, last paragraph as follows:

In addition, a Group III-V nitride semiconductor, containing gallium nitride as a main component, is used as a semiconductor material for the violet-light-emitting semiconductor laser device with an oscillation wavelength of about 400 nm. Alternatively, any of Group [II-IV] II-VI compound semiconductors such as zinc selenide (ZnSe), zinc sulfide (ZnS) and zinc oxide (Zno) may also be used.

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